

Origin of Spin Hall Effect (Reply to Comment)

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Theory of spin Hall effect developed in my Physical Review Letter [1] is based upon non-relativistic one-particle Hamiltonian with spin-orbit interaction to $1/c^2$:

$$\mathcal{H} = \frac{\mathbf{p}^2}{2m} + U(\mathbf{r}) + \frac{\hbar}{4m^2c^2} \boldsymbol{\sigma} \cdot (\nabla U \times \mathbf{p}) . \quad (1)$$

Here $U(\mathbf{r})$ is the electrostatic crystal potential felt by charge carriers. With an accuracy to $1/c^2$ Hamiltonian (1) is mathematically equivalent to

$$\mathcal{H} = \frac{1}{2m} \left(\mathbf{p} - \frac{e}{c} \mathbf{A}_\sigma \right)^2 + U(\mathbf{r}) \quad (2)$$

where

$$\mathbf{A}_\sigma \equiv -\frac{\hbar}{4emc} (\boldsymbol{\sigma} \times \nabla U) . \quad (3)$$

Consequently, the orbital motion of electrons is affected by the fictitious spin-dependent magnetic field:

$$\mathbf{B}_\sigma = \nabla \times \mathbf{A}_\sigma = -\frac{\hbar}{4emc} [\nabla \times (\boldsymbol{\sigma} \times \nabla U)] . \quad (4)$$

This fictitious field produces the same effect on the orbital motion of electrons as the real magnetic field does in the conventional Hall effect, but with the Hall currents having opposite directions for electrons with opposite spin polarizations.

Equations (1) - (4) provide conceptual framework needed to understand the spin Hall effect. According to Eq. (4), for the intrinsic spin Hall effect to exist, one needs to satisfy two requirements. First, charge carriers should be able to traverse the sample before scattering reverses their spin. This can be easily achieved in a small sample at low temperature. Second, $\nabla_i \nabla_j U$ should have a non-zero average over electron states. Since the homogeneous external electric field does not contribute to this average, the effect must be entirely due to the inhomogeneity of the crystal field. For a cubic crystal one obtains

$$\langle \nabla_i \nabla_j U \rangle = C \delta_{ij} \quad (5)$$

due to the cubic symmetry alone, with C being a constant. This constant was estimated in my Letter from the Laplace equation:

$$C \equiv \frac{1}{3} \langle \nabla^2 U(\mathbf{r}) \rangle = -\frac{4\pi}{3} e \langle \rho(\mathbf{r}) \rangle , \quad (6)$$

where $\rho(\mathbf{r})$ is the charge density that creates $U(\mathbf{r})$.

Kravchenko [2] argues that the right hand side of Eq. (6) must be zero due to electric neutrality of the solid. This argument is incorrect. It is contrary to the conventional approach to solids in which electron states are formed by the potential due to localized charges arranged in a crystal lattice [3]. Such a potential was chosen in my Letter. It is in line with the fact that spin-orbit interaction is large when electron passes close to the localized charge. *Electric neutrality, that is, the screening of the localized charges by conduction electrons, occurs at greater distances.* Taken literally, without relevance to the spatial scale, the electric neutrality would prohibit existence of solids. Without coupling of electrons to a localized (only partially screened) positive central charge even individual neutral atoms would not exist. In the same way, the screening of the localized charge by conduction electrons at large distances is irrelevant in the context of spin-orbit interaction in Eq. (1) that leads to the spin Hall effect.

In my Letter I chose $U(\mathbf{r})$ created by a cubic lattice of ions of charge $-Ze > 0$. For such a choice $\langle \rho \rangle = -Zen_0 = -en$ where n_0 and $n = Zn_0$ are concentrations of ions and conduction electrons, respectively. This gives

$$\langle \mathbf{B}_\sigma \rangle = \frac{4\pi}{3} n \mu_B \boldsymbol{\sigma} , \quad (7)$$

with μ_B being the Bohr magneton. As is shown in the Letter [1], this result provides the magnitude of spin Hall conductivity that is in quantitative agreement with experiments in cubic metals and semiconductors. Note that $\langle \mathbf{B}_\sigma \rangle$ depends on the crystal symmetry and should not be confused with the magnetic field created by polarized electrons. For, e.g., a tetragonal crystal, the average $\langle \nabla_i \nabla_j U \rangle$ should be of the form $C\delta_{ij} + Dn_in_j$ (with $\mathbf{n}$ being a tetragonal axis), which gives $\langle \mathbf{B}_\sigma \rangle$ of the form $C'\boldsymbol{\sigma} + D'(\mathbf{n} \cdot \boldsymbol{\sigma})\mathbf{n}$. Consequently, in a tetragonal crystal with polarized electrons, the electric current due to the external electric field should be

$$\mathbf{j} = \sigma_c \mathbf{E} + \sigma_{s1} [\boldsymbol{\xi} \times \mathbf{E}] + \sigma_{s2} (\boldsymbol{\xi} \cdot \mathbf{n}) [\mathbf{n} \times \mathbf{E}] , \quad (8)$$

where σ_c is charge conductivity, and σ_{s1}, σ_{s2} are two spin Hall conductivities; $\boldsymbol{\xi}$ being the polarization ($0 < \xi < 1$) of the electrons. Similar expressions can be obtained for crystal lattices of arbitrary symmetry. This prediction of the theory on how the spin Hall current depends on the

symmetry and orientation of the crystal can be tested in experiment.

The intrinsic spin Hall effect described above, and in my PRL [1], is a crystal counterpart of spin-dependent (Mott) scattering by individual (neutral) atoms [4]. Kravchenko's Comment fails to appreciate that both effects require spatial inhomogeneity of the electric field. This requirement was also ignored by researchers who employed the so-called Rashba spin-orbit interaction. The latter corresponds to Eq. (1) with ∇U replaced by a constant. While some argument in favor of such a replacement can be made for a purely two-dimensional electron system placed in a strong transverse electric field, it is certainly incorrect for a three-dimensional system. As can be seen from the above formulas, the replacement of ∇U with a constant results in $\mathbf{B}_\sigma = 0$. This makes

Rashba spin-orbit interaction unsuitable for the description of the intrinsic spin Hall effect.

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- [1] E. M. Chudnovsky, Phys. Rev. Lett. **99**, 206601 (2007).
 - [2] V. Ya. Kravchenko, preceding Comment, Phys. Rev. Lett. **100**, 199703 (2008).
 - [3] See, e.g., N. W. Ashcroft and N. D. Mermin, *Solid State Physics*, Chapter 8, (Holt, Rinehart, and Winston, New York, 1976).
 - [4] N. F. Mott, Proc. R. Soc. A **124**, 425 (1929).